

**REMARKS**

A Notice of Allowance was issued in this application on April 11, 2005.

Applicant hereby requests that allowed claim 8 in this application be amended as indicated above to correct an inadvertent typographical error in the spelling of the word "layer" and to clarifying language regarding the dopant concentration of the recited upper layer of p-doped epitaxial SiGe material, the dopant concentration of the upper layer being "at least about 10X lower" than the dopant concentration of the lower layer of p-doped epitaxial SiGe material. Applicant submits that these requested amendments to allowed claim 8 merely embody the correction of formal matters without changing the scope of allowed claim 8.

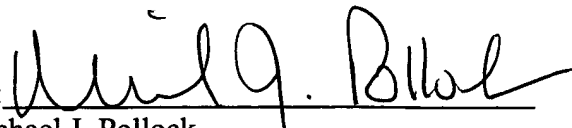
Applicant also requests that new claim 13 be added. New claim 13 depends directly from allowed claim 8. New claim 13 recites that the dopant concentration of the upper layer of p-doped epitaxial SiGe material is between 0 – 1E18, as disclosed in Applicant's specification. Applicant submits that, since new claim 13 depends from allowed claim 8, new claim 13 is also allowable. Therefore, the addition of new claim 13 merely embodies a formal matter without changing the scope of the allowed claims.

It is requested that the proposed amendments to the claims be approved and entered pursuant to 37 CFR §1.312.

Respectfully submitted,

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